

Silicon NPN Power Transistors

2SD546

DESCRIPTION

www.datasheet4u.com

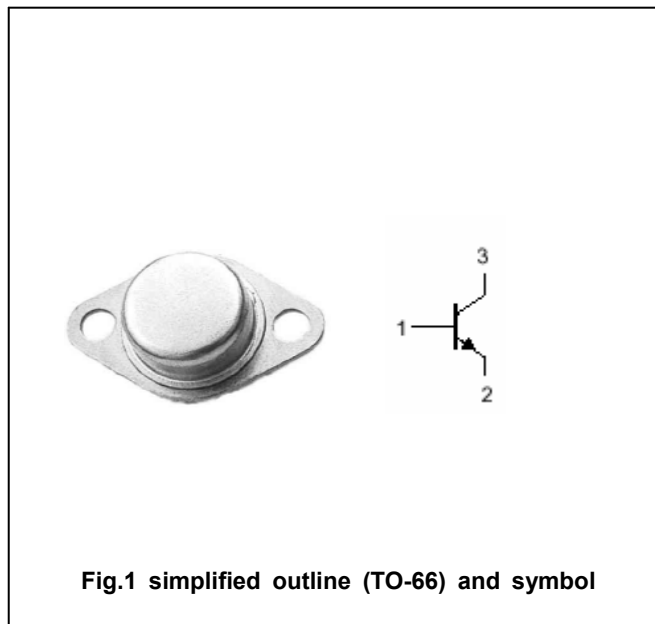
- With TO-66 package
- High breakdown voltage

APPLICATIONS

- Converters
- Inverters
- Switching regulators

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	800	V
V_{CEO}	Collector-emitter voltage	Open base	500	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		1	A
P_C	Collector power dissipation	$T_C = 25 \square$	30	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-55~150	$\square$

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CHARACTERISTICS

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 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C=30\text{mA}; I_B=0$	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1\text{mA}; I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=500\text{mA}; I_B=100\text{mA}$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=500\text{mA}; I_B=100\text{mA}$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=800\text{V}; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=6\text{V}; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=20\text{mA}; V_{CE}=10\text{V}$	40		200	
f_T	Transition frequency	$I_C=0.1\text{A}; V_{CE}=10\text{V}$		7		MHz

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PACKAGE OUTLINE

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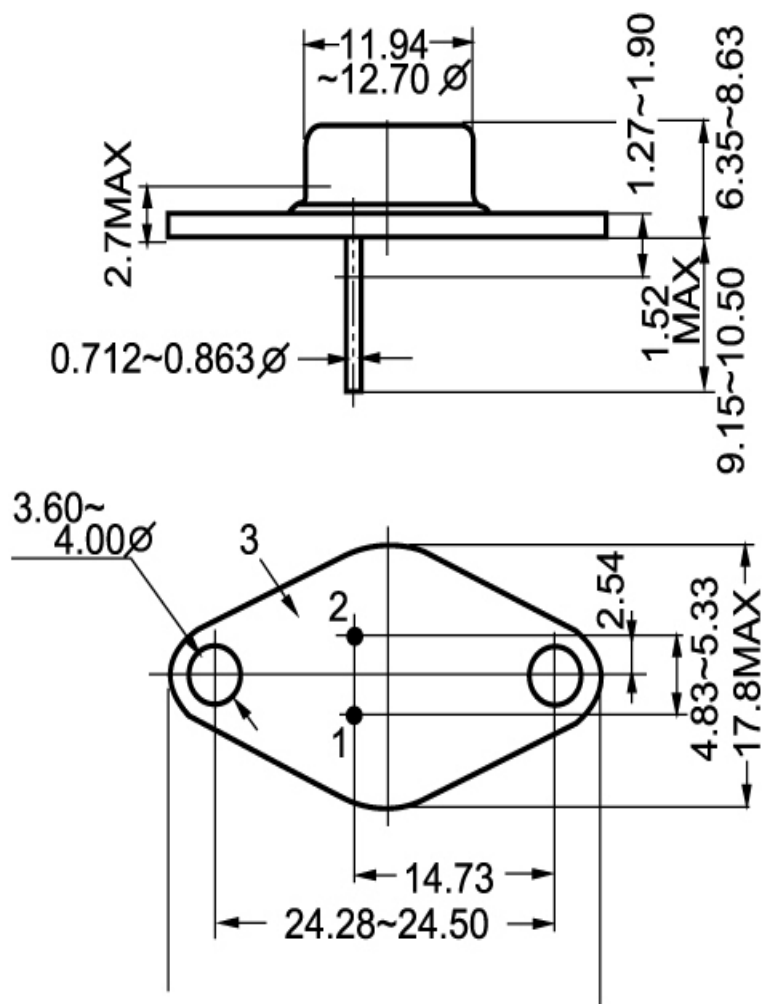


Fig.2 outline dimensions